AMENDMENTS TO THE CLAIMS

Claims 1-31 (Canceled).

32. (Previously Presented) A method of forming a capacitor in a semiconductor device, said method comprising:

forming a bottom conducting layer, wherein said bottom conducting layer forms a bottom electrode;

forming a dielectric layer over the bottom conducting layer, and annealing said dielectric layer with a first anneal process;

forming a top electrode with a top conducting layer over the annealed dielectric layer, wherein said top conducting layer is formed of a material selected from the group consisting of Platinum Rhodium (PtRh), Platinum Iridium (PtIr), Ruthenium Oxide (RuO_2), Rhodium Oxide (RhO_2), Chromium Oxide (CrO_2), Molybdenum Oxide (MoO_2), Rhemium Oxide (ReO_3), Iridium Oxide (IrO_2), Titanium Oxides (TiO_1 or TiO_2), Vanadium Oxides (VO_1 or VO_2), and Niobium Oxides (NbO_1 or NbO_2); and

annealing the top electrode with a second anneal process using an oxidizing gas anneal, said oxidizing gas anneal performed between 10 seconds to about 30 minutes.

33. (Original) A method of forming a capacitor of claim 32, wherein said capacitor is formed over a conductive plug, said method further comprising depositing an oxygen barrier over said conductive plug prior to forming the bottom conducting layer.

34. (Original) A method of forming a capacitor of claim 32, said method further comprising: annealing the dielectric layer after it is formed.

35. (Original) A method of forming a capacitor of claim 32, wherein said bottom conducting layer is formed of a material selected from the noble metal group.

36. (Original) A method of forming a capacitor of claim 32, wherein said bottom conducting layer is formed of a metal.

37. (Original) A method of forming a capacitor of claim 32, wherein said bottom conducting layer is formed of a metal alloy.

38. (Original) A method of forming a capacitor of claim 32, wherein said bottom conducting layer is formed of a conducting metal oxide.

39. (Original) A method of forming a capacitor of claim 32, wherein said bottom conducting layer is formed of a metal nitride.

40. (Original) A method of forming a capacitor of claim 32, wherein said bottom conducting layer is formed of a material selected from the group consisting of: Platinum (Pt), Platinum Rhodium (PtRh), Platinum Iridium (PtIr), Ruthenium, Ruthenium Oxide (RuO_2), Rhodium Oxide (RhO_2), Chromium Oxide (CrO_2), Molybdenum Oxide (MoO_2), Rhemium Oxide (ReO_3), Iridium Oxide (IrO_2), Titanium Oxides (TiO_1 or TiO_2), Vanadium Oxides (VO_1 or VO_2), Niobium Oxides (NbO_1 or NbO_2), and Tungsten Nitride (WNx, WN or W_2N).

41. (Original) A method of forming a capacitor of claim 40, wherein said bottom conducting layer is formed of a material selected from the group consisting of: Platinum (Pt), Platinum Rhodium (PtRh), Platinum Iridium (PtIr), and Tungsten Nitride (WNx, WN or W_2N).

42. (Original) A method of forming a capacitor of claim 32, wherein said dielectric layer is a dielectric metal oxide layer.

43. (Original) A method of forming a capacitor of claim 32, wherein said dielectric layer has a dielectric constant between 7 and 300.

44. (Original) A method of forming a capacitor of claim 32, wherein said dielectric layer is formed of a material selected from the group consisting of: Tantalum Oxide, Tantalum Pentoxide (Ta_2O_5), Barium Strontium Titanate (BST), Aluminum Oxide ($A1_2O_3$), Zirconium Oxide (ZrO_2), Praseodymium Oxide (PrO_2), Tungsten Oxide (WO_3), Niobium Pentoxide

(Nb_2O_5), Strontium Bismuth Tantalate (SBT), Hafnium Oxide (HfO_2), Hafnium Silicate, Lanthanum Oxide (La_2O_3), Yttrium Oxide (Y_2O_3), and Zirconium Silicate.

45. (Original) A method of forming a capacitor of claim 44, wherein said dielectric layer is formed of a material selected from the group consisting of: Tantalum Oxide, Tantalum Pentoxide (Ta_2O_5), Barium Strontium Titanate (BST), Strontium Bismuth Tantalate (BST), Aluminum Oxide (Al_2O_3), Zirconium Oxide (ZrO_2) and Hafnium Oxide (HfO_2).

46. (Original) A method of forming a capacitor of claim 45, wherein said dielectric layer is Tantalum Oxide and is crystalline or amorphous material.

47. (Previously Presented) A method of forming a capacitor of claim 45, wherein said dielectric layer is an amorphous dielectric layer which is heated to a temperature above 200 degrees Celsius to change said dielectric layer from an amorphous material to a crystalline material.

48. (cancelled)

49. (cancelled)

50. (cancelled)

51. (Canceled)

52. (cancelled)

53. (Previously Presented) A method of forming a capacitor of claim 32, wherein said bottom and top conducting layers are formed of a material selected from the group consisting of: Platinum Rhodium (PtRh), or Platinum Indium (PtIr) and said dielectric layer is a layer of Tantalum Oxide.

54. (Previously Presented) A method of forming a capacitor of claim 32, wherein said bottom and top conducting layers are formed of a material selected from the group

consisting of: Platinum Rhodium (PtRh), or Platinum Iridium (PtIr) and said dielectric layer is a layer of Barium Strontium Titanate (BST) or Strontium Bismuth Tantalate (SBT).

55. (Previously Presented) A method of forming a capacitor of claim 32, wherein said top conducting layers are formed of a material selected from the group consisting of Platinum Rhodium (PtRh), or Platinum Iridium (PtIr) and, said bottom conducting layer is a layer of Tungsten Nitride (WNx, WN or W_2N) layer, and said dielectric layer is a layer of Aluminum Oxide (Al_2O_3).

56. (Canceled).

57. (Previously Presented) A method of forming a capacitor of claim 32, wherein said annealing is performed with a material selected from the group consisting of: Oxygen (O_2), Ozone (O_3), Nitrous Oxide (N_2O), Nitric Oxide (NO), and water vapor (H_2O).

58. (Original) A method of forming a capacitor of claim 57, wherein said annealing is performed with a gas mixture containing at least one element selected from the group consisting: Oxygen (O_2), Ozone (O_3), Nitrous Oxide (N_2O), Nitric Oxide (NO), and water vapor (H_20).

59. (Previously Presented) A method of forming a capacitor of claim 32, wherein said annealing is a plasma enhanced annealing.

60. (Original) A method of forming a capacitor of claim 59, wherein said annealing is a remote plasma enhanced annealing.

61. (Previously Presented) A method of forming a capacitor of claim 32, wherein said annealing is an ultraviolet light enhanced annealing.

62. (Original) A method of forming a capacitor of claim 32, wherein said annealing is performed at a temperature between 300 and 800 degrees Celsius.

63. (Original) A method of forming a capacitor of claim 62, wherein said annealing is performed at a temperature between 400 and 750 degrees Celsius.

64. (Canceled).

65. (currently amended) A method of forming a capacitor of claim [[64]] 62, wherein said annealing is performed at a pressure between 2 and 660 Torr.

Claims 66-67 (Canceled).

68. (Previously Presented) A method of forming a capacitor of claim 32, wherein said annealing is performed in the presence of an oxygen gas with a flow rate between 0.01 and 10 liters per second.

Claims 69-96 (Canceled).

97. (Previously Presented) A method of forming a capacitor in a semiconductor device, said method comprising:

forming a bottom electrode;

forming a dielectric layer over the bottom electrode;

forming a top electrode over said dielectric layer; and

annealing said top electrode with an oxidizing gas anneal at a temperature greater than 400°C.

98. (Previously Presented) A method of forming a capacitor in a semiconductor device, said method comprising:

forming a bottom electrode;

forming a dielectric layer over the bottom electrode;

annealing the dielectric layer with a first oxidizing gas anneal for about 10 seconds to about 60 minutes, at a temperature from about 300 to about 800°C;

forming a top electrode over said annealed dielectric layer; and annealing said top electrode with a second oxidizing gas anneal for about 10 seconds to about 60 minutes, at a temperature from about 300 to about 800°C.